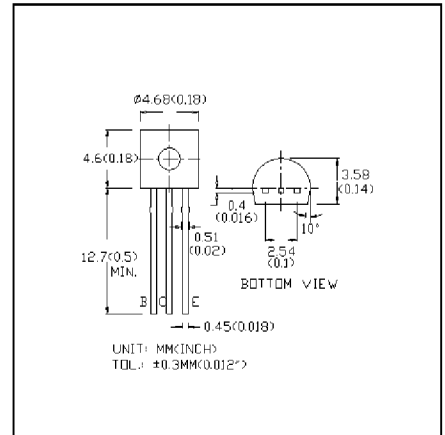


#### DESCRIPTION

2N5367 is PNP silicon planar transistor use in general purpose consumer and industrial amplifier and switching applications.



#### ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	$V_{CBO}$	40V
Collector-Emmitter Voltage	$V_{CBO}$	40V
Emitter-Base Voltage	$V_{EBO}$	4V
Collector Current	$I_C$	300mA
Continuous Power Dissipation	$P_d$	360mW
Operating & Storage Junction Temperature	$T_j, T_{stg}$	-55 to +150°C

#### ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS	
Collector-Emmitter Breakdown Voltage	$LV_{CBO}^*$	40		V	$I_C = 10mA$	$I_B = 0$
Collector Cutoff Current	$I_{CBO}$		100	nA	$V_{CB} = 40V$	$I_B = 0$
Collector Cutoff Current	$I_{CES}$		100	nA	$V_{CB} = 40V$	$V_{EB} = 0$
Emtter Cutoff Current	$I_{EBO}$		10	$\mu A$	$V_{EB} = 4V$	$I_C = 0$
D.C. Current Gain	$H_{FE}^*$	200			$I_C = 2mA$	$V_{CE} = 10V$
		250	500		$I_C = 50mA$	$V_{CE} = 1V$
		75			$I_C = 300mA$	$V_{CE} = 5V$
Base-Emmitter Voltage	$V_{BE}$		0.8	V	$I_C = 2mA$	$V_{CE} = 10V$
Collector-Emmitter Saturation Voltage	$V_{CE(sat)}^*$		0.25	V	$I_C = 50mA$	$I_B = 2.5mA$
			1	V	$I_C = 300mA$	$I_B = 30mA$
Base-Emmitter Saturation Voltage	$V_{BE(sat)}^*$		1.1	V	$I_C = 50mA$	$I_B = 2.5mA$
			2	V	$I_C = 300mA$	$I_B = 30mA$
Small Signal Current Gain	$h_{fe}$	200			$I_C = 2mA$	$V_{CE} = 10V$
						$f = 1kHz$
Output Capacitance	$C_{ob}$		8	pF	$V_{CB} = 10V$	$f = 1MHz$
Input Capacitance	$C_{ib}$		35	pF	$V_{EB} = 0.5V$	$f = 1MHz$
Current Gain-Bandwidth Product	$f_T$	200	TYP	pF	$I_C = 2mA$	$V_{CE} = 10V$

\* Pulse test : pulse width  $< 300\mu S$ , duty cycle  $< 2\%$ .



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